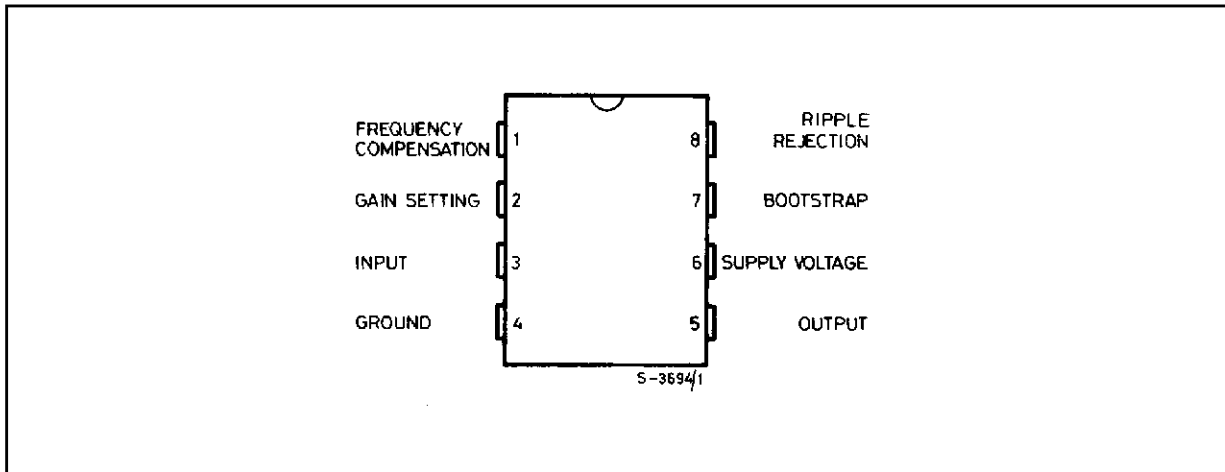


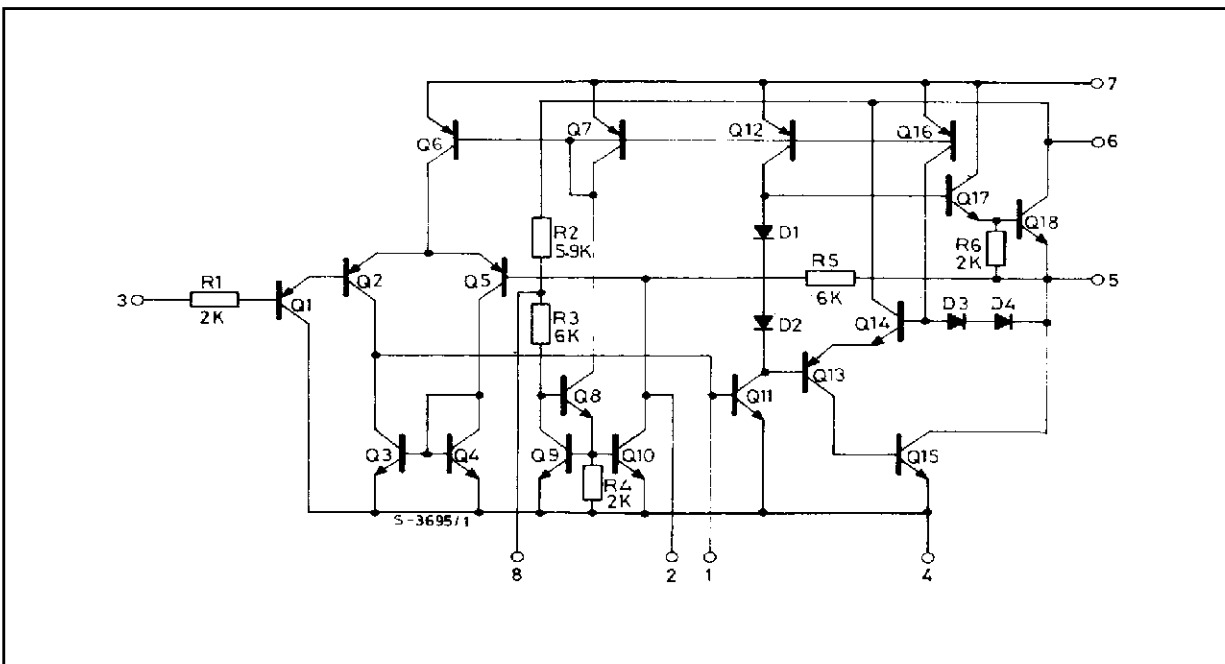


# TBA820M

## PIN CONNECTION (top view)



## SCHEMATIC DIAGRAM



## THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th-j-amb}$	Thermal resistance junction-ambient	max 100	°C/W

**ELECTRICAL CHARACTERISTICS** (Refer to the test circuits  $V_s = 9V$ ,  $T_{amb} = 25\text{ }^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_s$	Supply voltage		3		16	V
$V_o$	Quiescent output voltage (pin 5)		4	4.5	5	V
$I_d$	Quiescent drain current			4	12	mA
$I_b$	Bias current (pin 3)			0.1		$\mu\text{A}$
$P_o$	Output power	$d = 10\%$ $R_f = 120\Omega$ $V_s = 12V$ $V_s = 9V$ $V_s = 9V$ $V_s = 6V$ $V_s = 3.5V$	$f = 1\text{ kHz}$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 4\Omega$	0.9	2 1.6 1.2 0.75 0.25	W W W W W
$R_i$	Input resistance (pin 3)	$f = 1\text{ kHz}$		5		$\text{M}\Omega$
$B$	Frequency response (-3 dB)	$R_L = 8\Omega$ $C_5 = 1000\ \mu\text{F}$ $R_f = 120\Omega$	$C_B = 680\ \text{pF}$ $C_B = 220\ \text{pF}$	25 to 7,000 25 to 20,000		Hz
$d$	Distortion	$P_o = 500\ \text{mW}$ $R_L = 8\Omega$ $f = 1\text{ kHz}$	$R_f = 33\Omega$ $R_f = 120\Omega$	0.8 0.4		%
$G_v$	Voltage gain (open loop)	$f = 1\text{ kHz}$ $R_L = 8\Omega$		75		dB
$G_v$	Voltage gain (closed loop)	$R_L = 8\Omega$ $f = 1\text{ kHz}$	$R_f = 33\Omega$ $R_f = 120\Omega$	45 34		dB
$e_N$	Input noise voltage (*)			3		$\mu\text{V}$
$i_N$	Input noise current (*)			0.4		nA
$\frac{S+N}{N}$	Signal to noise ratio (*)	$P_o = 1.2W$ $R_L = 8\Omega$ $G_v = 34\ \text{dB}$	$R_1 = 10K\Omega$ $R_1 = 50\ \text{k}\Omega$	80 70		dB
SVR	Supply voltage rejection (test circuit of fig. 2)	$R_L = 8\Omega$ $f_{(\text{ripple})} = 100\ \text{Hz}$ $C_6 = 47\ \mu\text{F}$ $R_f = 120\Omega$		42		dB

(\*) B = 22 Hz to 22 KHz

Figure 3. Output power vs. supply voltage

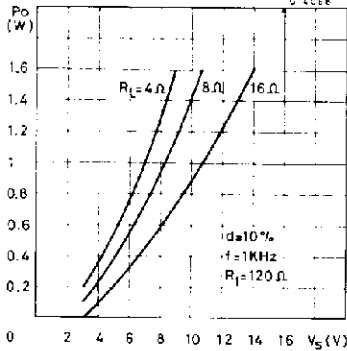


Figure 4. Harmonic distortion vs. output power

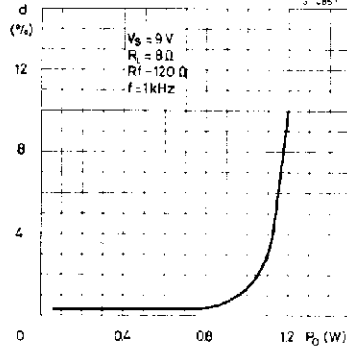


Figure 5. Power dissipation and efficiency vs. output power

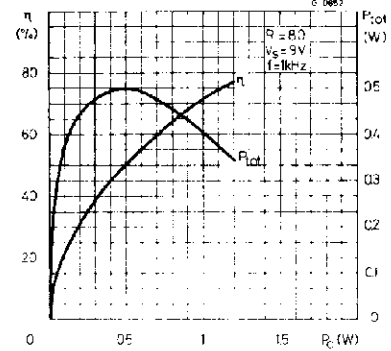


Figure 6. Maximum power dissipation (sine wave operation)

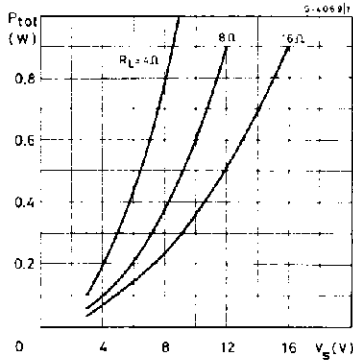


Figure 7. Suggested value of CB vs. Rf

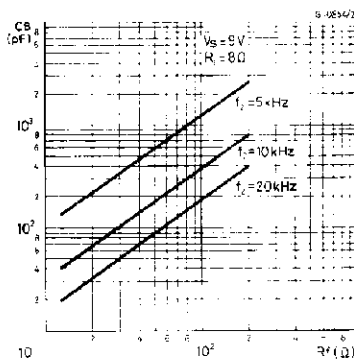


Figure 8. Frequency response

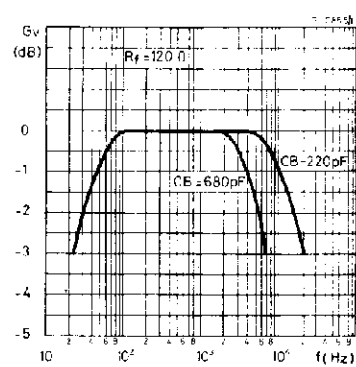


Figure 9. Harmonic distortion vs. frequency

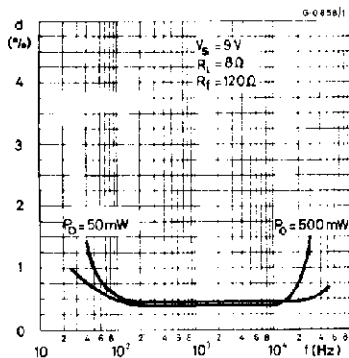


Figure 10. Supply voltage rejection (Fig. 2 circuit)

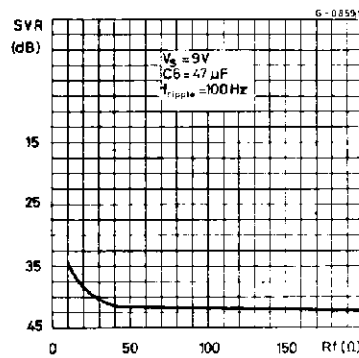
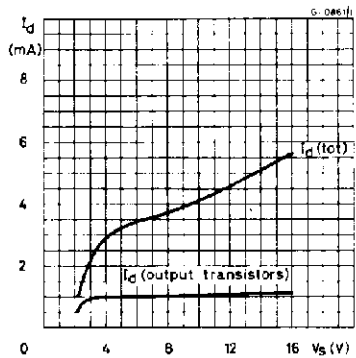
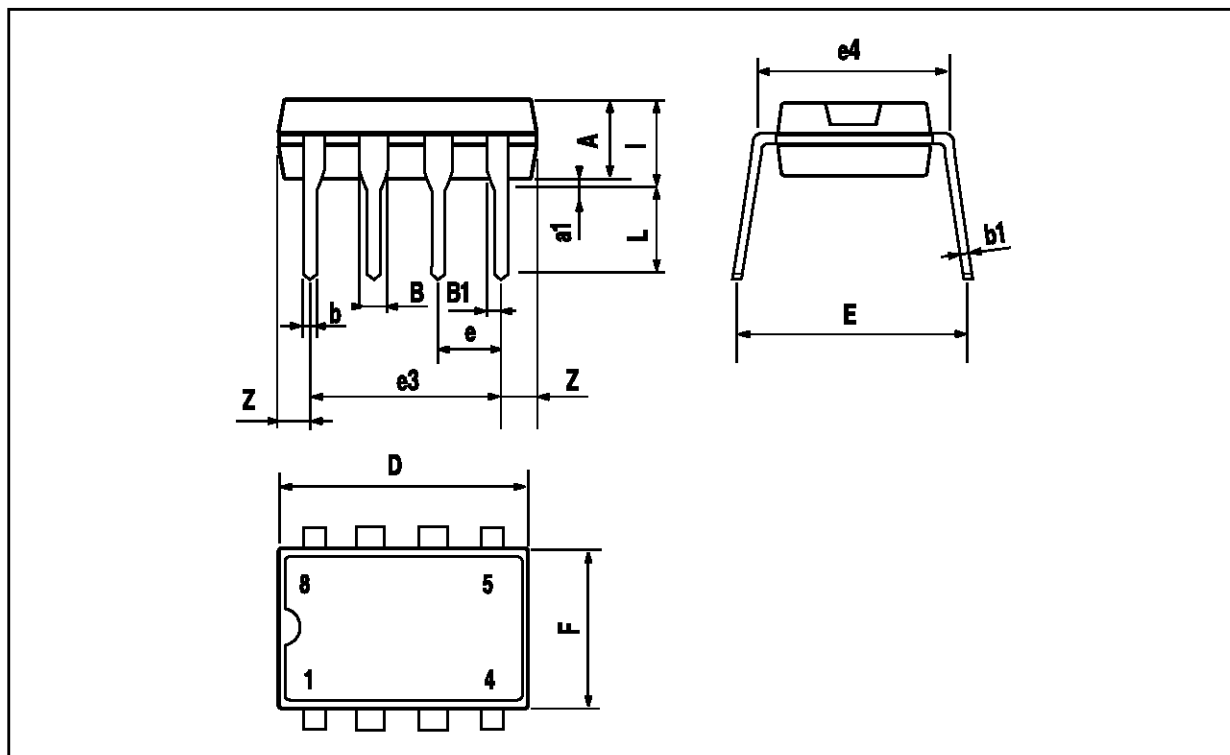


Figure 11. Quiescent current vs. supply voltage



MINIDIP PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
I			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060



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